
IN THE SPECIFICATION

A¹ Next, second photoresist layer (260) is formed over the substrate, including the opening formed in the previous step, and patterned with the image of a line to form a second photoresist mask with a trench (270) as shown in Fig. 2d. The line pattern is next transferred from the second photoresist mask into the second dielectric layer by etching and stopping on etch-stop layer (225). This is accomplished by etching the second low-k dielectric layer by using a recipe comprising C₂F₆, C₄F₈, Ar, N₂ and O₂. It will be noted that the low-k protection layer (250) is also removed from the bottom of hole opening (245) thereby exposing the underlying passivation layer, while leaving the protective layer on the vertical walls of the hole, as seen in Fig. 2e. Then passivation layer (215) is removed from the bottom of the hole opening using a recipe comprising C₂F₆, C₄F₈, Ar, N₂ and O₂ and exposing the underlying first metal layer (210), as shown in Fig. 2f. This is followed by the removal of the second photoresist layer, hence completing the forming of a damascene structure having a composite hole (245) and line (270) pattern as shown in Fig. 2f.

IN THE CLAIMS

Please amend the following claims as follows:

A² 10. (AMENDED ONCE) The method of claim 1, wherein said barrier layer comprises Ta, Ti, TaN, TiSiN, TaSiN, or WN.
